

Figure S1. Surface morphologies of the samples treated with RIE followed by HF/NH₄F etching. Left: 1- μ m RIE and 1- μ m HF/NH₄F etching, middle: 1- μ m RIE and 2- μ m HF/NH₄F etching, right: 1- μ m RIE and 3- μ m HF/NH₄F etching. The results showed that there was no obvious difference in surface morphology among the three HF/NH₄F-etched sample surfaces.

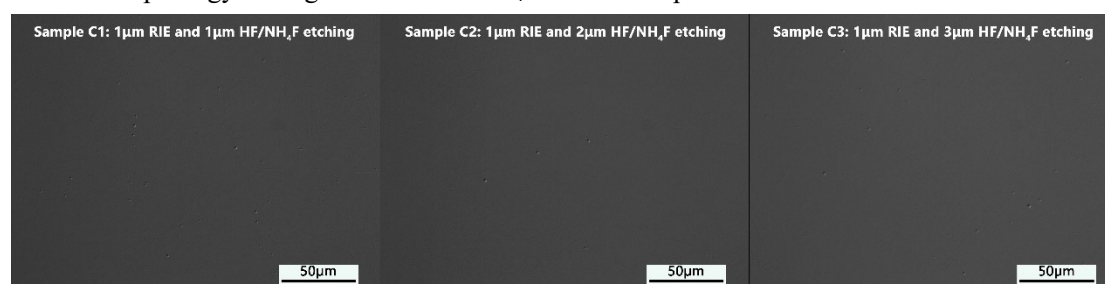


Figure S2. Raw data of the SC imaging for the six combined-etched samples. Left column: RIE and HF etching with removal amount of 1 μ m, 2 μ m, and 3 μ m. Right column: RIE and HF/NH₄F etching with removal amounts of 1 μ m, 2 μ m, and 3 μ m.

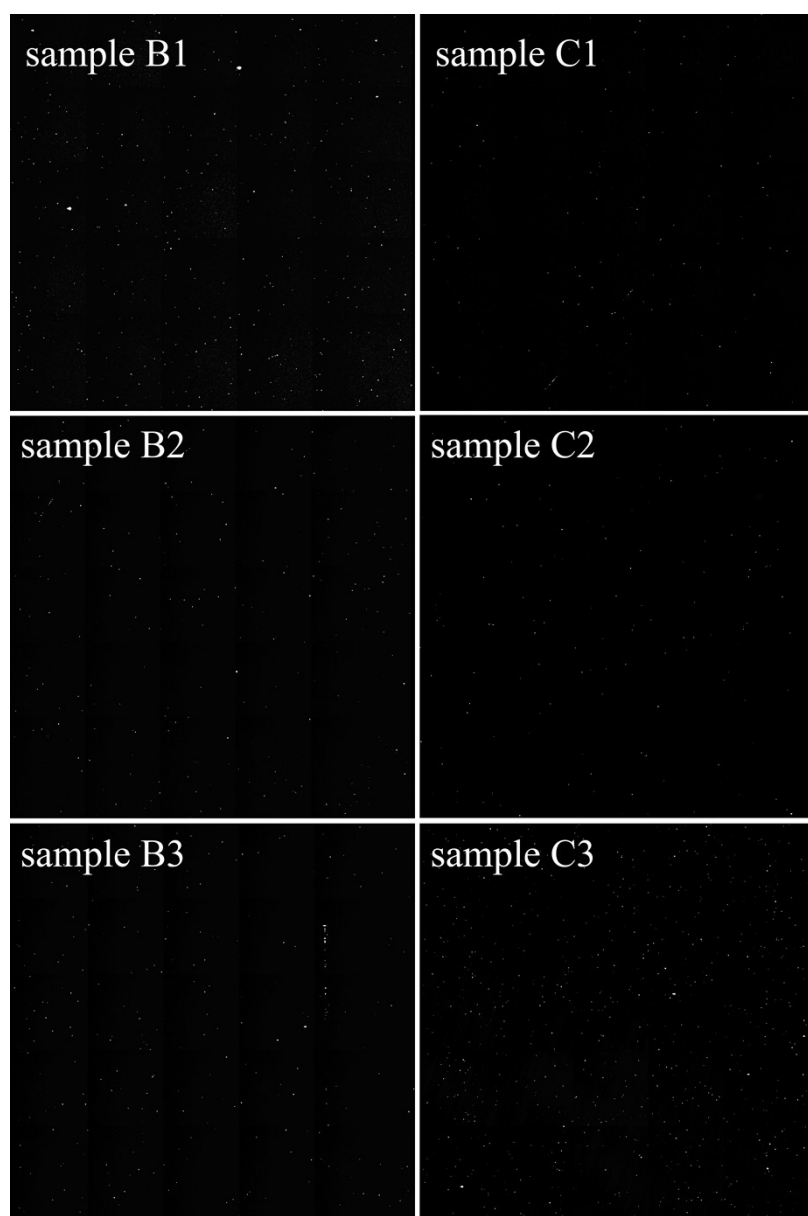


Figure S3. Statistical data of the SC imaging for the six combined-etched samples. Left column: RIE and HF etching with removal amount of 1 μm , 2 μm , and 3 μm . Right column: RIE and HF/ NH_4F etching with removal amounts of 1 μm , 2 μm , and 3 μm .

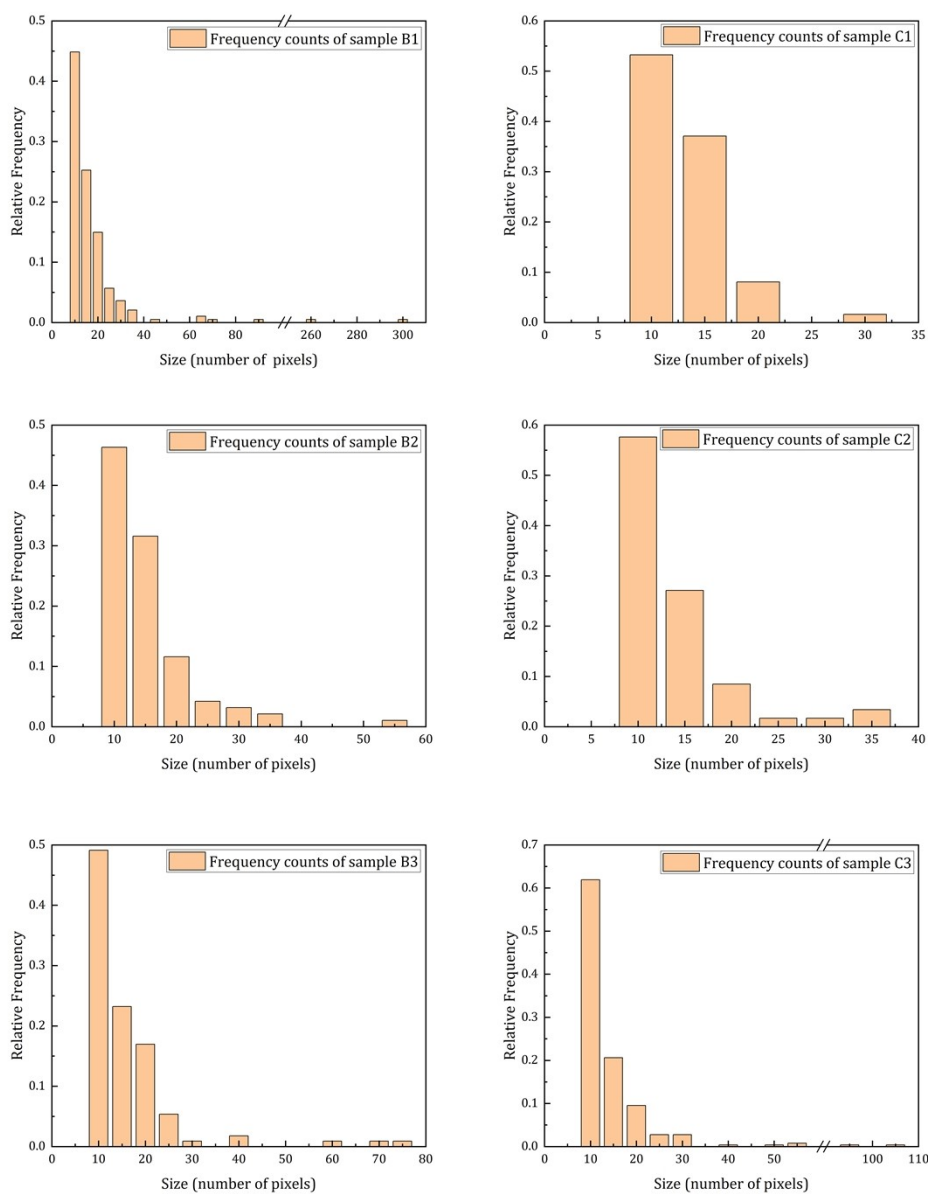


Figure S4. Raw data of the SC imaging for sample C3 (1- μm RIE and 3- μm HF/ NH_4F etching).

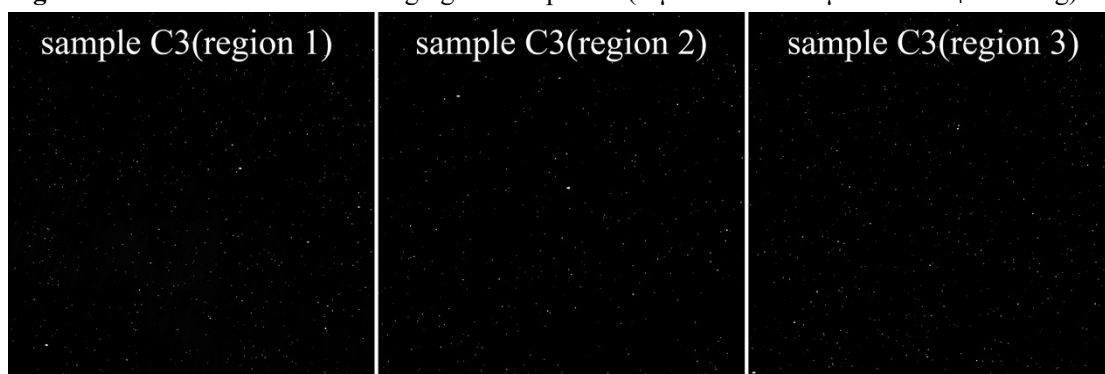


Figure S5. Statistical data of the SC imaging for sample C3 (1- μm RIE and 3- μm HF/ NH_4F etching).

